

Title (en)
VERTICAL SIC MOSFET

Title (de)
VERTIKALER SIC-MOSFET

Title (fr)
MOSFET SIC VERTICAL

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Application
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Abstract (en)
[origin: WO2017167469A1] The invention relates to a vertical SiC MOSFET (20) comprising a source connection (2), a drain connection (4) and a gate region (36) as well as an epitaxial layer (22) arranged between the source connection (2) and the drain connection (4) and comprising a first-type doping, where a horizontally extending intermediate layer (24) comprising regions (40) having a second-type doping different from the first-type doping is embedded in the epitaxial layer (22). The vertical SiC MOSFET (20) is characterised in that at least the regions with a second type of doping (40) are electroconductively connected to the source connection (2). The gate region (36) can be arranged in a gate trench (39).

IPC 8 full level
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Citation (search report)
See references of WO 2017167469A1

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